

TOSHIBA

2SA1736

TOSHIBA TRANSISTOR SILICON PNP EPITAXIAL TYPE (PCT PROCESS)

2SA1736

POWER AMPLIFIER APPLICATIONS

POWER SWITCHING APPLICATIONS

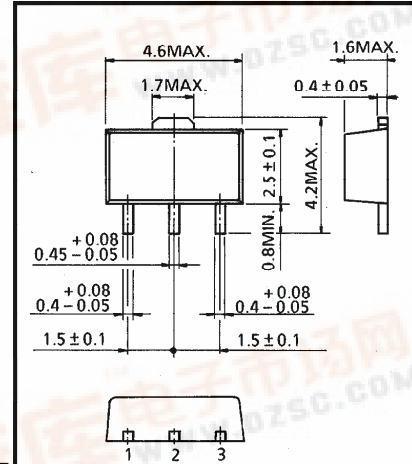
- Low Saturation Voltage: $V_{CE(sat)} = -0.5V$ (Max.) ($I_C = -1.5A$)
- High Speed Switching : $t_{stg} = 0.2\mu s$ (Typ.)
- Small Flat Package
- $P_C = 1\sim 2W$ (Mounted on Ceramic Substrate)
- Complementary to 2SC4541

MAXIMUM RATINGS ($T_a = 25^\circ C$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	-60	V
Collector-Emitter Voltage	V_{CEO}	-50	V
Emitter-Base Voltage	V_{EBO}	-6	V
Collector Current	I_C	-3	A
Base Current	I_B	-0.6	A
Collector Power Dissipation	P_C	500	mW
Collector Power Dissipation	P_C^*	1000	mW
Junction Temperature	T_j	150	$^\circ C$
Storage Temperature Range	T_{stg}	-55~150	$^\circ C$

* : Mounted on ceramic substrate ($250mm^2 \times 0.8t$)

Unit in mm



1. BASE
2. COLLECTOR (HEAT SINK)
3. EMITTER

PW-MINI

JEDEC

EIAJ

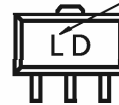
SC-62

TOSHIBA 2-5K1A

Weight : 0.05g

Marking

Type Name



961001FAA2

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ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT			
Collector Cut-off Current	I_{CBO}	$V_{CB} = -60V, I_E = 0$	—	—	-0.1	μA			
Emitter Cut-off Current	I_{EBO}	$V_{EB} = -6V, I_C = 0$	—	—	-0.1	μA			
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = -10mA, I_E = 0$	-50	—	—	V			
DC Current Gain	$h_{FE(1)}$	$V_{CE} = -2V, I_C = -100mA$	120	—	400				
	$h_{FE(2)}$	$V_{CE} = -2V, I_C = -2A$	40	—	—				
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = -1.5A, I_B = -75mA$	—	—	-0.5	V			
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = -1.5A, I_B = -75mA$	—	—	-1.2	V			
Transition Frequency	f_T	$V_{CE} = -2V, I_C = -100mA$	—	100	—	MHz			
Collector Output Capacitance	C_{ob}	$V_{CB} = -10V, I_E = 0, f = 1MHz$	—	32	—	pF			
Switching Time	Turn-on Time	t_{on}	<p> $20\mu s$ $-I_{B1} = I_{B2} = 75mA,$ DUTY CYCLE $\leq 1\%$ </p>			—	0.1	—	μs
	Storage Time	t_{stg}				—	0.2	—	
	Fall Time	t_f				—	0.1	—	

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